

Abstracts

An Osciplier Up to K-Band Using Dual-Gate GaAs MESFET

A.S. Chu and P.T. Chen. "An Osciplier Up to K-Band Using Dual-Gate GaAs MESFET." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 383-386.

The feasibility of using a dual-gate GaAs MESFET with Mo-Au gates as a Ku or K-band osciplier has been demonstrated. Two test oscipliers were measured, one osciplier in Ku-band delivered 16.3 dBm at 12 GHz, while the other in K-band offered 9.0 dBm output power at 18.2 GHz and 3.8 dBm at 22 GHz.

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